# MMBC1622D8 NPN EPITAXIAL SILICON TRANSISTOR

T-29-19

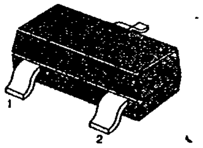
## AMPLIFIER TRANSISTOR

## ABSOLUTE MAXIMUM RATINGS ($T_a=25°C$)

| Characteristic | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | 40 | V |
| Collector-Emitter Voltage | $V_{CEO}$ | 35 | V |
| Emitter-Base Voltage | $V_{EBO}$ | 5.0 | V |
| Collector Current | $I_C$ | 100 | mA |
| Collector Dissipation | $P_C$ | 350 | mW |
| Storage Temperature | Tstg | 150 | °C |

- Refer to MMBC1622D6 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

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## ELECTRICAL CHARACTERISTICS ($T_a=25°C$)

| Characteristic | Symbol | Test Condition | Min | Max | Unit |
|---|---|---|---|---|---|
| Collector Cutoff Current | $I_{CBO}$ | $V_{CB}=25V$, $I_E=0$ | | 50 | nA |
| Emitter Cutoff Current | $I_{EBO}$ | $V_{EB}=5V$, $I_C=0$ | | 50 | nA |
| DC Current Gain | $h_{FE}$ | $V_{CE}=3V$, $I_C=0.1mA$ | 150 | | |
| | | $V_{CE}=3V$, $I_C=0.5mA$ | 450 | 900 | |
| Collector-Emitter Saturation Voltage | $V_{CE}$ (sat) | $I_C=100mA$, $I_B=10mA$ | | 0.3 | V |
| Base-Emitter On Voltage | $V_{BE}$ (on) | $I_C=0.5mA$, $V_{CE}=3V$ | 0.55 | 0.65 | V |
| Current Gain-Bandwidth Product | $f_T$ | $V_{CE}=6V$, $I_E=1mA$<br>$f=100MHz$ | 100 | | MHz |

Marking